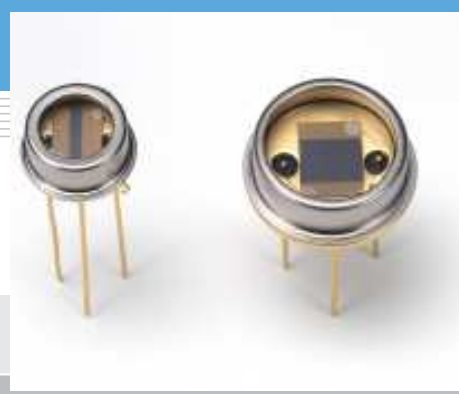


PbS photoconductive detector

P9217 series

Room-temperature detectors capable of detecting up to 2.9 μm



P9217 is a PbS photoconductive detector with greatly improved stability and resistance to high temperatures as compared with conventional types.

Features

- High reliability: high temperature resistant

Applications

- Radiation thermometers
- Flame monitors
- Water content analyzers
- Food ingredient analysis
- Spectrophotometers

Accessories (Optional)

- Preamplifier for PbS/PbSe photoconductive detector C3757-02

■ Specification/Absolute maximum ratings

Type No.	Dimensional Outline/ Window material *1	Package	Cooling	Active area (mm)	Absolute maximum ratings		
					Supply voltage (V)	Operating temperature Topr (°C)	Storage temperature Tstg (°C)
P9217	①/K	TO-5	Non-cooled	1 × 5	100	-30 to +65	-55 to +65
P9217-02	①/K			2 × 2			
P9217-03	①/K			3 × 3			
P9217-04	②/K	TO-8		4 × 5			

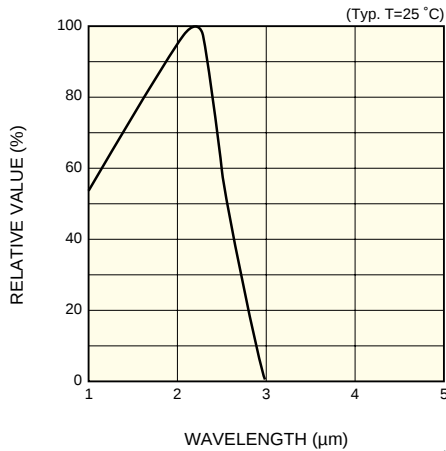
■ Electrical and optical characteristics (Typ. unless otherwise noted)

Type No.	Peak sensitivity wavelength λ_p (μm)	Cut-off wavelength λ_c (μm)	Photo sensitivity *2 S $\lambda = \lambda_p$ $V_s = 15 \text{ V}$		D* (500, 600, 1)		D* (λ_p , 600, 1) ($\text{cm} \cdot \text{Hz}^{1/2}/\text{W}$)	Rise time t_r 0 to 63 % Max. (μs)	Dark resistance R_d ($\text{M}\Omega$)
			Min. (V/W)	Typ. (V/W)	Min. ($\text{cm} \cdot \text{Hz}^{1/2}/\text{W}$)	Typ. ($\text{cm} \cdot \text{Hz}^{1/2}/\text{W}$)			
P9217	2.2	2.9	4×10^4	1×10^5	5×10^8	1×10^9	1×10^{11}	200	0.05 to 1
P9217-02			5×10^4						0.25 to 2.5
P9217-03			2×10^4						0.25 to 2.5
P9217-04			1×10^4		2×10^8	5×10^8	5×10^{10}		0.2 to 2.0

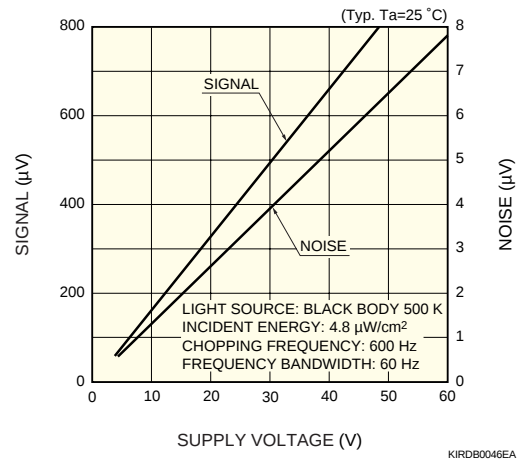
*1: Window material K: Borosilicate glass

*2: Chopping frequency: 600 Hz, load resistance: nearly equal to detector element dark resistance.

Spectral response

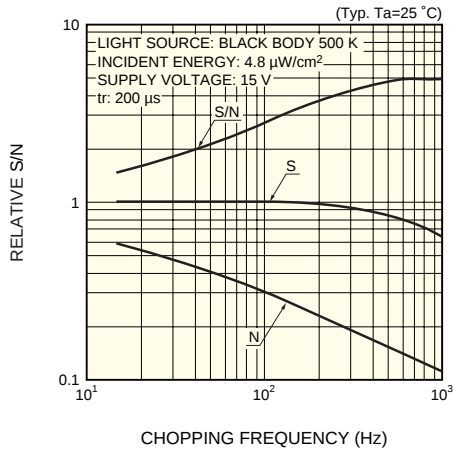


S/N vs. supply voltage



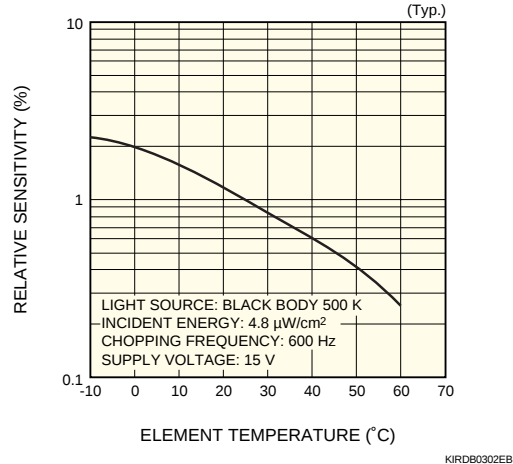
If voltage of higher than 60 V is applied, the noise increases exponentially, degrading the S/N. The device should be operated at 60 V or less.

S/N vs. chopping frequency



Increasing the chopping frequency reduces the $1/f$ noise and results in an S/N improvement. The S/N can also be improved by narrowing the noise bandwidth using a lock-in amplifier.

Photo sensitivity temperature characteristic



Cooling the device enhances its sensitivity, but the sensitivity also depends on the load resistance in the circuit.

Dark resistance, rise time temperature characteristics

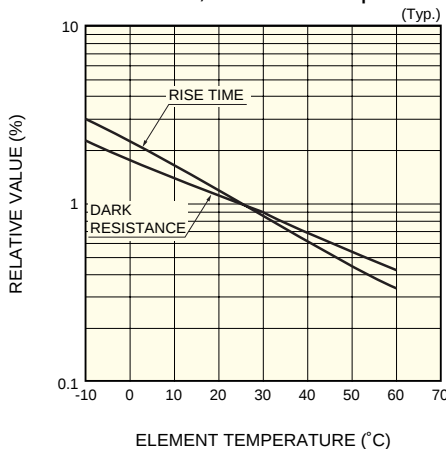
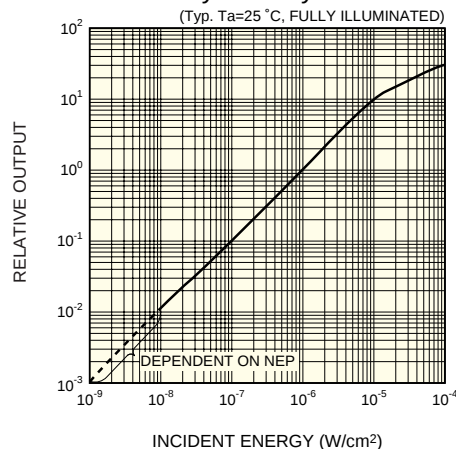


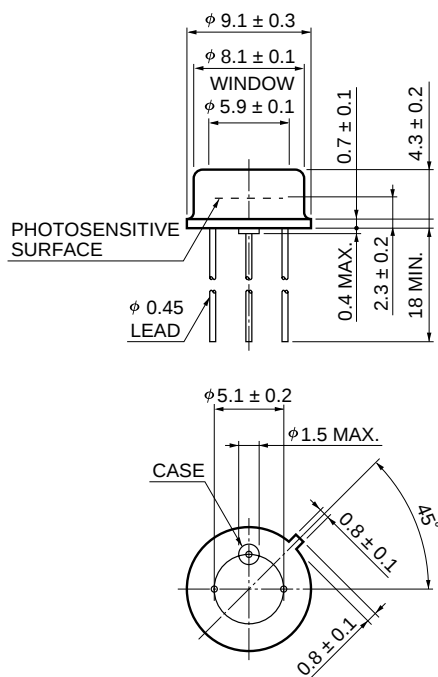
Photo sensitivity linearity



By making the incident light spot smaller than the active area, the upper limit of the linearity becomes lower.

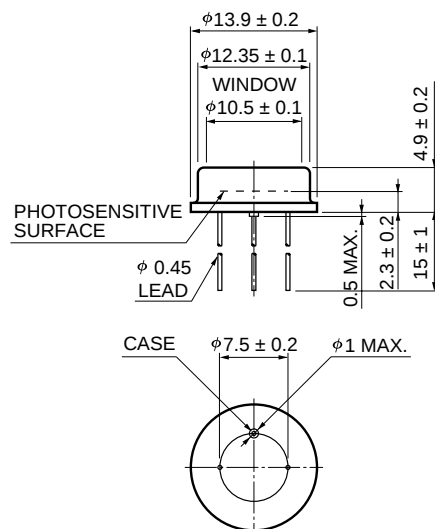
■ Dimensional outline (unit: mm)

① P9217/-02/-03



KIRDA0166EB

② P9217-04



KIRDA0181EA

HAMAMATSU

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